Application Number 10/599131
Response to the Ex Parte Quayle Office Action dated September 15, 2009

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of manufacturing a conductive pattern, comprising the steps of:

(i) forming a molecular film of at least one kind of molecule on a part of a conductive film by placing, on the conductive film, a solution in which the at least one kind of molecule has been dissolved, the one kind of molecule being selected from the group consisting of:

a molecule that is expressed by Formula (1):

$CF_3(CF_2)_n(CH_2)_mSH$ [[...]] (1),

where *n* indicates a natural number in a range of 3 to 7 while *m* denotes a natural number in a range of 8 to 18; and

a molecule that is expressed by Formula (2):

$CF_3(CF_2)_p(CH_2)_qSS(CH_2)_{q'}(CF_2)_{p'}CF_3$ [[...]] (2),

where p and p' each are a natural number in a range of 3 to 7 independently while q and q' each are a natural number in a range of 8 to 18 independently, and

(ii) removing the conductive film located in a part where the molecular film has not been formed, by bringing the conductive film into contact with an etchant for the conductive film.

2. (Original) The method of manufacturing a conductive pattern according to claim 1, wherein the conductive film includes at least one selected from the group consisting of gold, silver, copper, platinum, gallium arsenide, and indium phosphide.

3. (Original) The method of manufacturing a conductive pattern according to claim 1, wherein the conductive film is formed on a resin substrate.

4. (Currently Amended) A method of manufacturing an electronic device including a conductive pattern, the method comprising the steps of:

(I) forming a molecular film of at least one kind of molecule on a part of a conductive film by placing, on the conductive film, a solution in which the at least one kind of molecule has been dissolved, the one kind of molecule being selected from the group consisting of:

a molecule that is expressed by Formula (1):

$CF_3(CF_2)_n(CH_2)_mSH$ [[...]] (1),

where *n* indicates a natural number in a range of 3 to 7 while m denotes a natural number in a range of 8 to 18; and

a molecule that is expressed by Formula (2):

$CF_3(CF_2)_p(CH_2)_qSS(CH_2)_{q'}(CF_2)_{p'}CF_3$ [[...]] (2),

where p and p' each are a natural number in a range of 3 to 7 independently while q and q' each are a natural number in a range of 8 to 18 independently, and

(II) forming the conductive pattern by bringing the conductive film into contact with an etchant for the conductive film and thereby removing the conductive film located in a part where the molecular film has not been formed.

5. (Original) The method of manufacturing an electronic device according to claim 4, wherein the conductive film includes at least one selected from the group consisting of gold, silver, copper, platinum, gallium arsenide, and indium phosphide.

6. (Original) The method of manufacturing an electronic device according to claim 4, wherein the conductive film is formed on a resin substrate.

7. (Original) The method of manufacturing an electronic device according to claim 4, wherein the electronic device is a field effect transistor and the conductive pattern comprises a source electrode and a drain electrode.

8. (Original) The method of manufacturing an electronic device according to claim 7, further comprising, after the step (II),

(III) forming an organic semiconductor film between the source electrode and the drain electrode by placing a solution between the source electrode and the drain electrode, the solution including an organic semiconductor material dissolved therein.

9-13. (Cancelled)